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Patent Abstracts of Japan

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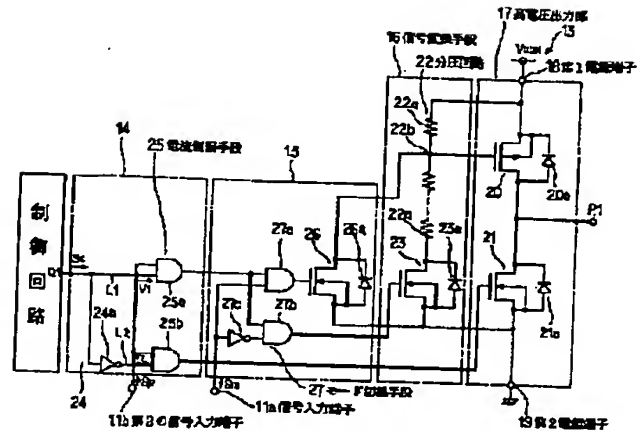
APPLICATION DATE : 20-05-98
APPLICATION NUMBER : 10138323

APPLICANT : DENSO CORP;

INVENTOR : HIRANO TETSUO;

INT.CL. : G09G 3/20 G09G 3/30

TITLE : LOAD DRIVING DEVICE



ABSTRACT : PROBLEM TO BE SOLVED: To enable performing easily a test of an internal function despite of constitution in which a high breakdown voltage semiconductor switching element is included in an output stage turned on when high voltage is applied in an actual use state.

SOLUTION: A MOSFET 20 in a high voltage output section 17 of an output stage is turned on by a voltage divided signal S_d outputted from a voltage dividing circuit 22 in an on-state of a MOSFET 23 in a voltage level conversion section 16, and a MOSFET 21 in a high voltage output section 17 is turned on by a second voltage signal V_2 given from a through current control section 14. A low voltage operation control section 15 has a MOSFET 26 connecting an output terminal 22b of the voltage dividing circuit 22 to a second power source terminal 19 in an on-state and a signal switching circuit 27 which can switch a normal use mode or a test mode by a mode switching signal S_m given to a mode switching terminal 11a. A signal switching circuit 27 gives a first voltage signal V_1 given from the through current control section 14 to a MOSFET 26 when the device is in a test mode, and gives a first voltage signal V_1 to a MOSFET 23 when the device is in a normal use mode.

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